IRFE9130 (JANTX2N6849U)

PD-91716E

Repetitive Avalanche and dv/dt Rated Power MOSFET
Surface Mount (LCC-18)
-100V, -6.5A, P-channel

Features

- Surface mount
- Small footprint
- Alternative to TO-39 Package
- Hermetically sealed
- Dynamic dv/dt rating
- Avalanche energy rating
- Simple drive requirements
- Light weight
- ESD rating: Class 1C per MIL-STD-750, Method 1020

Product Summary

- **BV_{DSS}:** -100V
- **I_D:** -6.5A
- **$R_{DS(on),max}$:** 0.30Ω
- **$Q_{G,max}$:** 34.8nC
- **REF:** MIL-PRF-19500/564

LCC-18

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified to JANTX screening flow according to MIL-PRF-19500 for high-reliability applications

Description

The leadless chip carrier (LCC) package represents the logical next step in the continual evolution of surface mount technology. Desinged to be a close replacement for the TO-39 package, the LCC will give designers the extra flexibility they need to increase circuit board density. IR HiRel has engineered the LCC package to meet the specific needs of the power market by increasing the size of the bottom source pad, thereby enhancing the thermal and electrical performance. The lid of the package is grounded to the source to reduce RF interference.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level
IRFE9130	LCC-18	COTS
JANTX2N6849U	LCC-18	JANTX
JANTXV2N6849U	LCC-18	JANTXV

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1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
I_{D1} @ V_{GS} = -10V, T_C = 25°C	Continuous Drain Current	-6.5	A
I_{D2} @ V_{GS} = -10V, T_C = 100°C	Continuous Drain Current	-4.1	A
I_{DM} @ T_C = 25°C	Pulsed Drain Current [1]	-25	A
P_D @ T_C = 25°C	Maximum Power Dissipation	25	W
	Linear Derating Factor	0.20	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy [2]	165	mJ
I_{AR}	Avalanche Current [1]	-6.5	A
E_{AR}	Repetitive Avalanche Energy [1]	2.5	mJ
dv/dt	Peak Diode Reverse Recovery [3]	-5.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Lead Temperature	300 (for 5s)	
	Weight	0.42 (Typical)	g

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.

[2] V_{DD} = -25V, starting T_J = 25°C, Peak I_L = -6.5A

[3] $I_{SD} \leq$ -6.5A, di/dt $\leq$ -390A/µs, $V_{DD} \leq$ -100 V, $T_J \leq$ 150°C, Suggested Rg =7.5Ω

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2 Device Characteristics

2.1 Electrical Characteristics

Table 3 Static and Dynamic Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V_{GS} = 0V, I_D =-1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.10	—	V/°C	Reference to 25°C, I_D = -1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.30	Ω	V_{GS} =-10 V, I_{D2} = -4.1A [1]
		—	—	0.32		V_{GS} = -10V, I_{D2} = -6.5A [1]
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -250µA
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-25	µA	V_{DS} = -80V, V_{GS} = 0V
		—	—	-250		V_{DS} =- 80V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V_{GS} =- 20V
	Gate-to-Source Leakage Reverse	—	—	100		V_{GS} = 20V
Q_G	Total Gate Charge		—	34.8	nC	I_{D1} = -6.5A V_{DS} = -50V V_{GS} = -10V
Q_{GS}	Gate-to-Source Charge		—	6.8		
Q_{GD}	Gate-to-Drain ('Miller') Charge		—	23.1		
$t_{d(on)}$	Turn-On Delay Time	—	—	60	ns	I_{D1} = -6.5A ** V_{DD} = -40V R_G = 7.5Ω V_{GS} = -10V
t_r	Rise Time	—	—	140		
$t_{d(off)}$	Turn-Off Delay Time	—	—	140		
t_f	Fall Time	—	—	140		
$L_s + L_D$	Total Inductance	—	6.1	—	nH	Measured from the center of drain pad to center of source pad
C_{iss}	Input Capacitance	—	790	—	pF	V_{GS} = 0V V_{DS} = -25V f = 1.0MHz
C_{oss}	Output Capacitance	—	340	—		
C_{rss}	Reverse Transfer Capacitance	—	71	—		

** Switching speed maximum limits are based on manufacturing test equipment and capability.

[1] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

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2.2 Source-Drain Diode Ratings and Characteristics

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-6.5	A	
I_{SM}	Pulsed Source Current (Body Diode) [1]	—	—	-25	A	
V_{SD}	Diode Forward Voltage	—	—	-4.3	V	T_J = 25°C, I_S = -6.5A, V_{GS} = 0V [2]
t_{rr}	Reverse Recovery Time	—	—	250	ns	T_J = 25°C, I_F = -6.5A, V_{DD} ≤ -50V di/dt = -100A/µs
Q_{rr}	Reverse Recovery Charge	—	2.0	—	µC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	5.0	°C/W
$R_{\theta J\text{-}PCB}$	Junction-to-PC Board (Soldered to a copper clad PC board)	—	—	19	

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.

[2] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

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3 Electrical Characteristics Curves

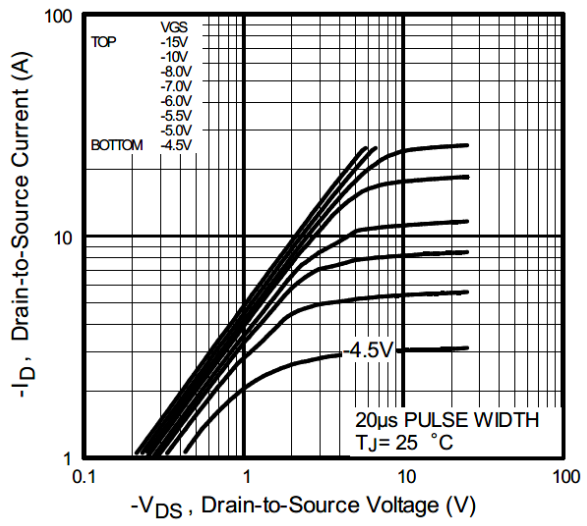

Figure 1 Typical Output Characteristics

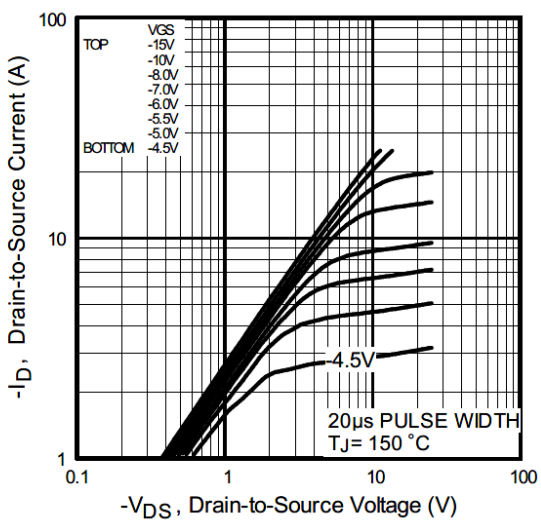

Figure 2 Typical Output Characteristics

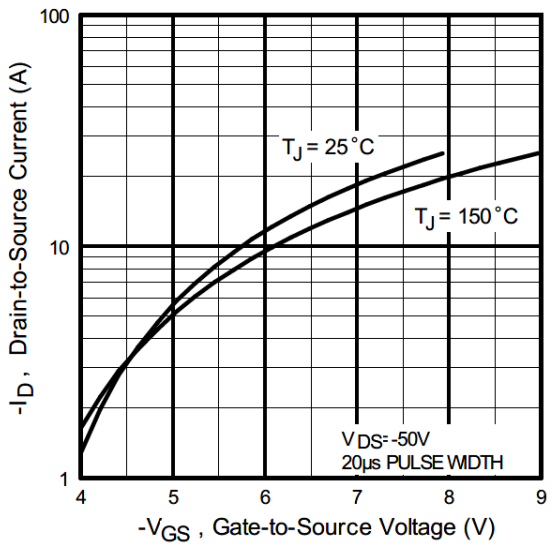

Figure 3 Typical Transfer Characteristics

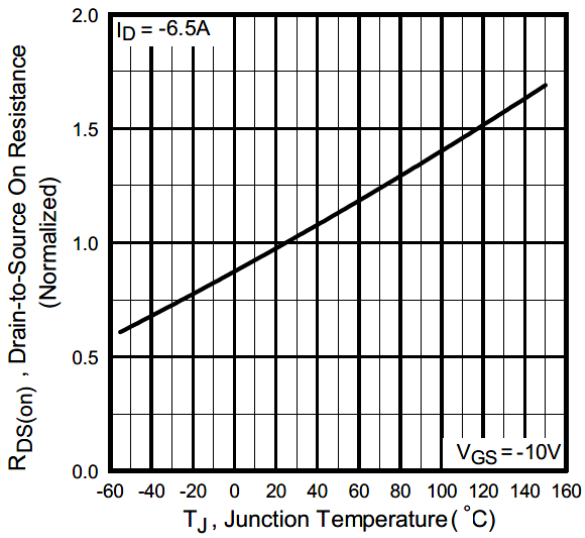

Figure 4 Normalized On-Resistance Vs. Temperature

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Electrical Characteristics Curves

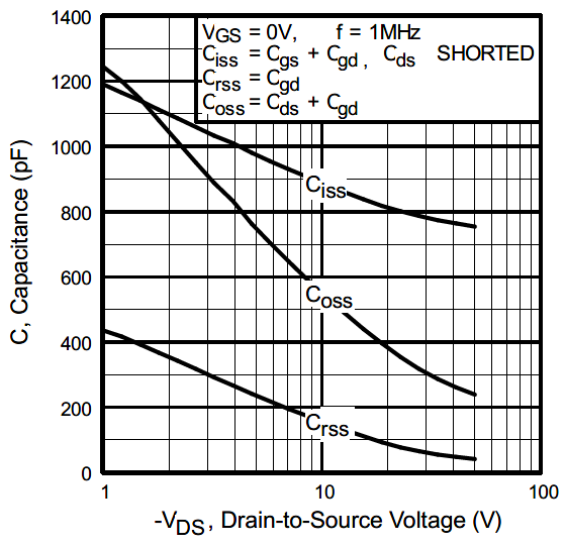

Figure 5 **Typical Capacitance Vs. Drain-to-Source Voltage**

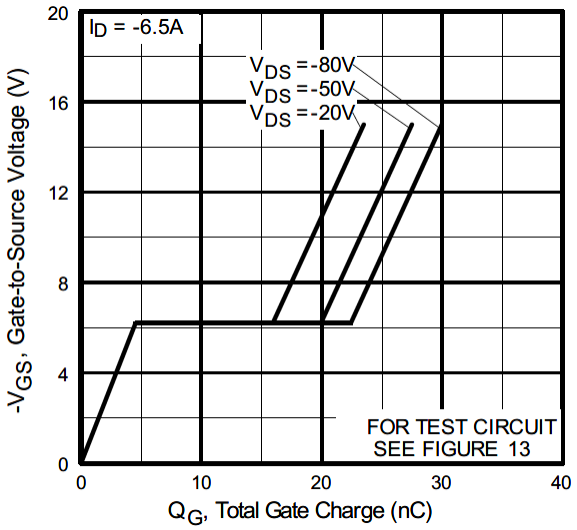

Figure 6 **Typical Gate Charge Vs. Gate-to-Source Voltage**

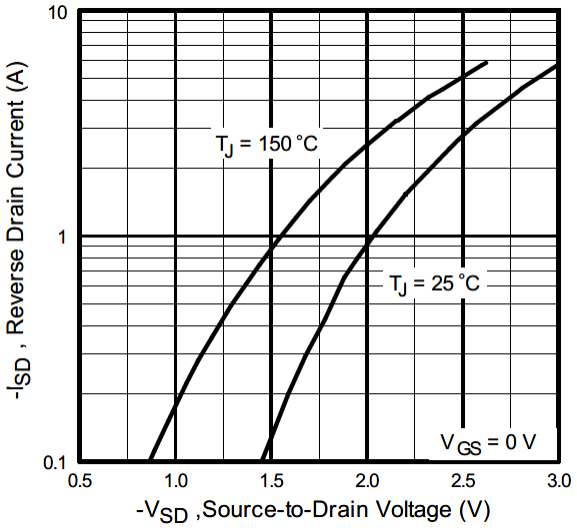

Figure 7 **Typical Source-Drain Diode Forward Voltage**

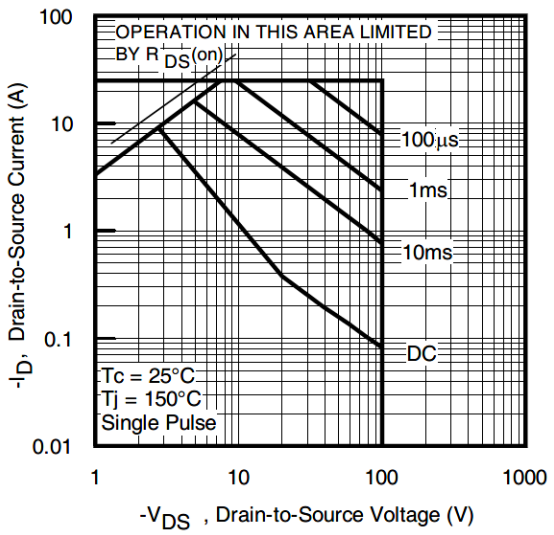

Figure 8 **Maximum Safe Operating Area**

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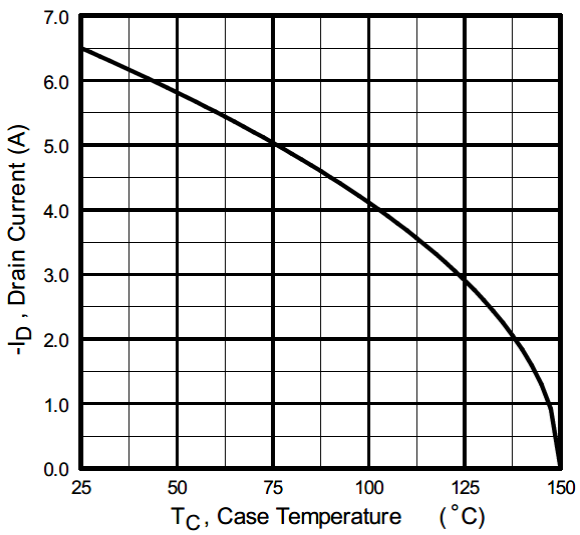

Figure 9 **Maximum Drain Current Vs. Case Temperature**

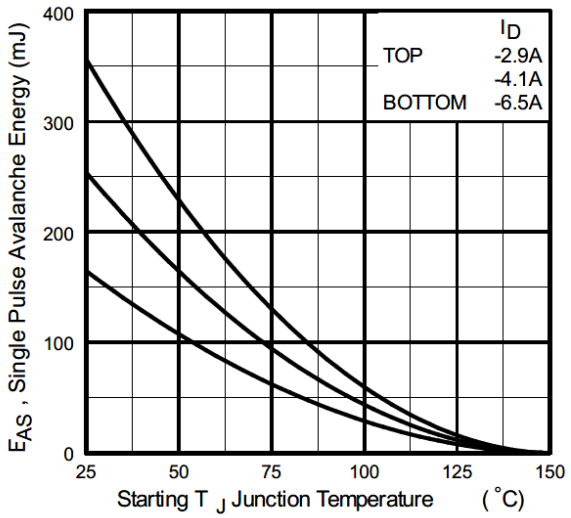

Figure 10 **Maximum Avalanche Energy Vs. Junction Temperature**

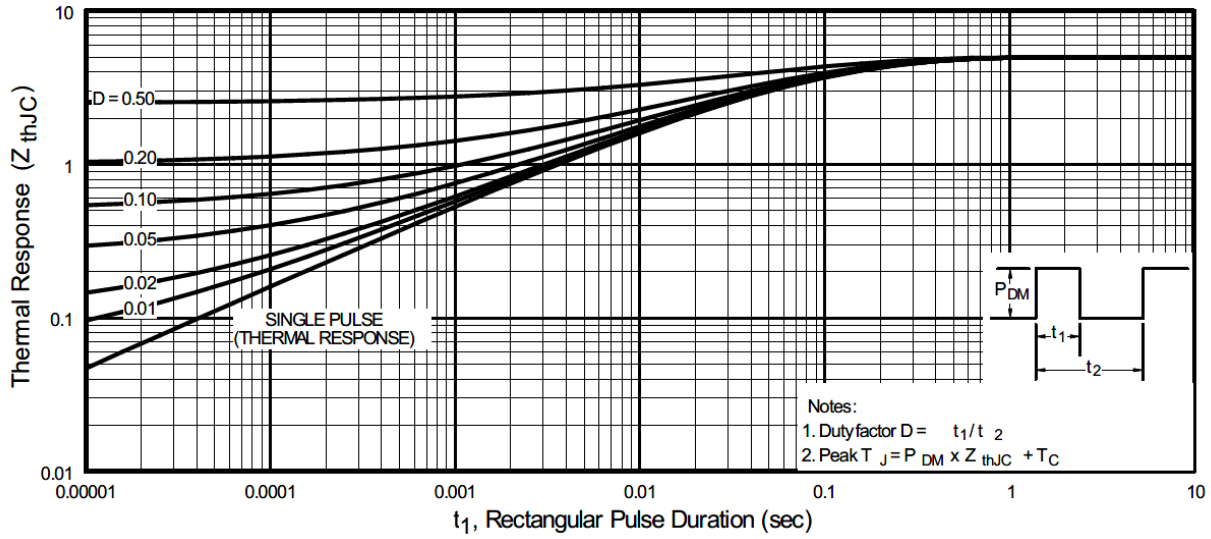

Figure 11 **Maximum Effective Transient Thermal Impedance, Junction-to-Case**

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4 Test Circuits

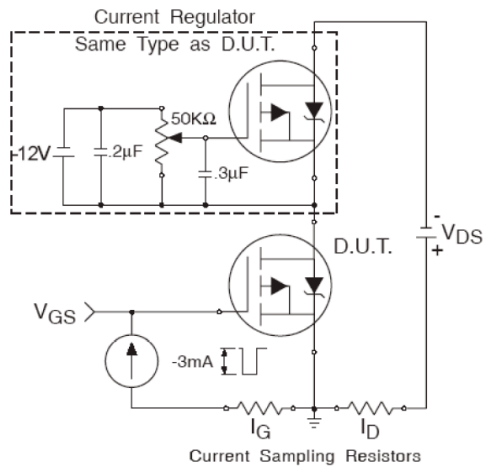

Figure 12 Gate Charge Test Circuit

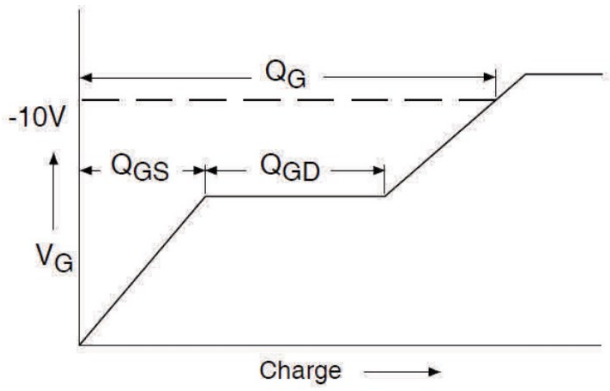

Figure 13 Gate Charge Waveform

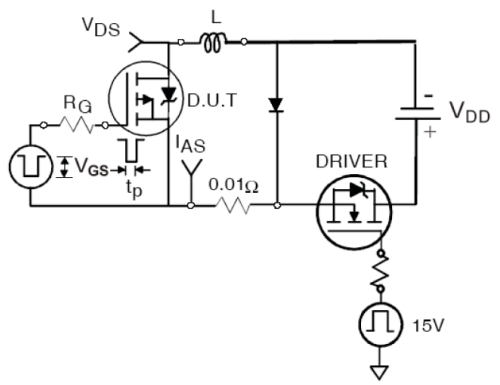

Figure 14 Unclamped Inductive Test Circuit

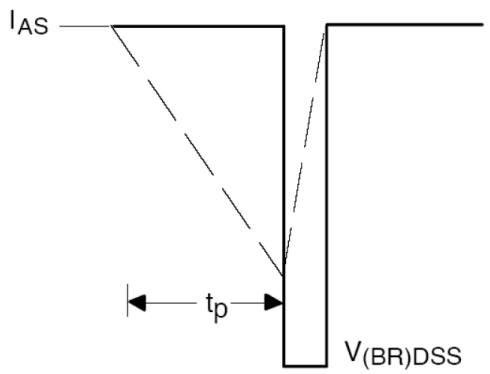

Figure 15 Unclamped Inductive Waveform

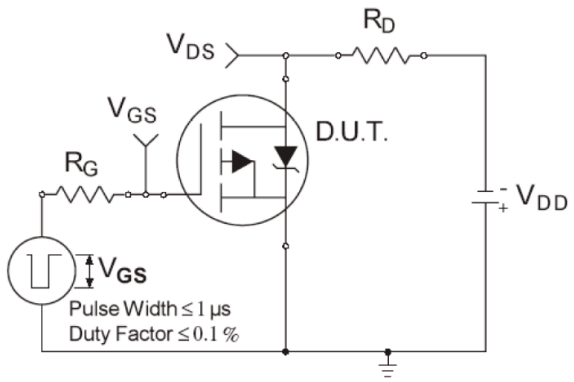

Figure 16 Switching Time Test Circuit

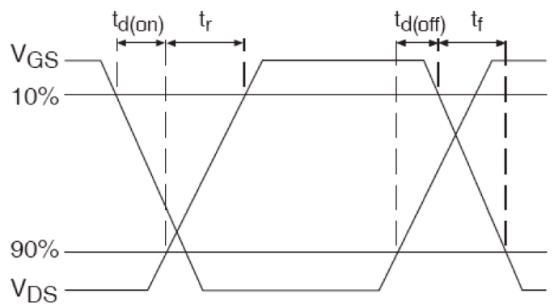

Figure 17 Switching Time Waveforms

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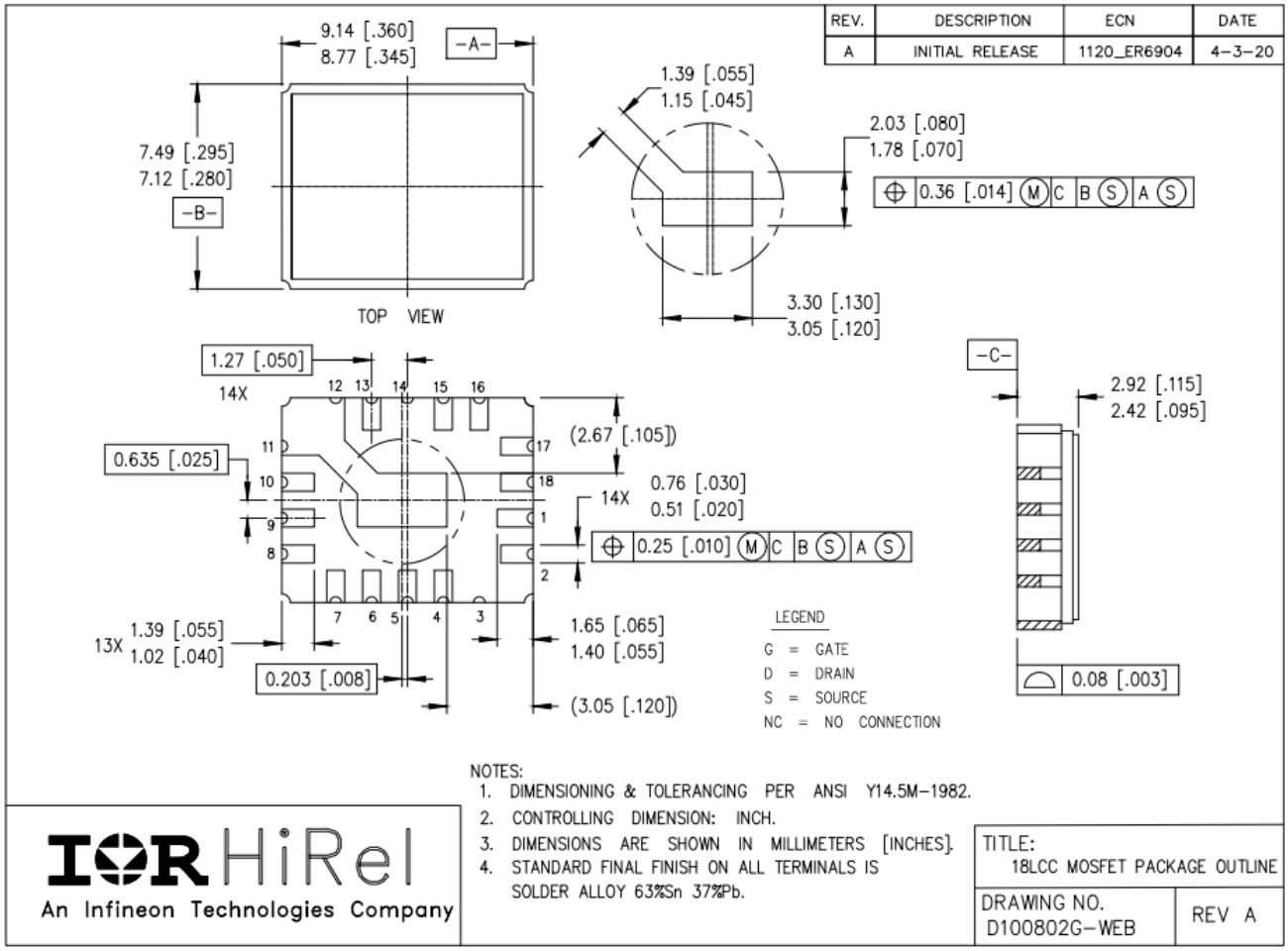
5 Package Outline

Note: For the most updated package outline, please see the website: [LCC-18]



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Revision history

Document version	Date of release	Description of changes
	01/25/2001	Datasheet (PD-91716B)
Rev C	07/28/2015	Updated based on ECN-1120_03204
Rev D	02/17/2019	Updated based on ECN-1120_06822
Rev E	12/06/2024	Updated based on ECN-1120_10116

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